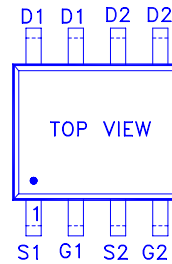
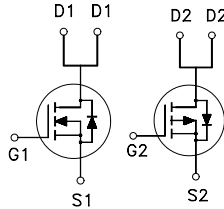


PRODUCT SUMMARY

	$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
N-Channel	30	60mΩ	4A
P-Channel	-30	45mΩ	-5A



G : GATE
D : DRAIN
S : SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	N-Channel	P-Channel	UNITS
Drain-Source Voltage		V_{DS}	30	-30	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	I_D	4	-5	A
	$T_C = 70\text{ }^\circ\text{C}$		3	-4	
Pulsed Drain Current ¹		I_{DM}	12	-20	
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	2		W
	$T_C = 70\text{ }^\circ\text{C}$		1.3		
Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	°C / W

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT	
			MIN	TYP	MAX		
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	N-Ch	30		V	
		$V_{GS} = 0V, I_D = -250\mu A$	P-Ch	-30			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	N-Ch	1	1.5		2.5
		$V_{DS} = V_{GS}, I_D = -250\mu A$	P-Ch	-1	-1.5		-2.5

Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	N-Ch			± 100	nA
		$V_{DS} = 0V, V_{GS} = \pm 20V$	P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$	N-Ch			1	μA
		$V_{DS} = -24V, V_{GS} = 0V$	P-Ch			-1	
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 55^\circ C$	N-Ch			10	
		$V_{DS} = -20V, V_{GS} = 0V, T_J = 55^\circ C$	P-Ch			-10	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	N-Ch	12			A
		$V_{DS} = -5V, V_{GS} = -10V$	P-Ch	-20			
Drain-Source Resistance ¹	On-State $R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 3A$	N-Ch		72	95	$m\Omega$
		$V_{GS} = -4.5V, I_D = -4A$	P-Ch		58	80	
		$V_{GS} = 10V, I_D = 4A$	N-Ch		48	60	
		$V_{GS} = -10V, I_D = -5A$	P-Ch		34	45	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 3A$	N-Ch		19		S
		$V_{DS} = -5V, I_D = -5A$	P-Ch		11		

DYNAMIC

Input Capacitance	C_{iss}	N-Channel	N-Ch		790		pF
			P-Ch		690		
Output Capacitance	C_{oss}	$V_{GS} = 0V, V_{DS} = 10V, f = 1MHz$	N-Ch		175		pF
			P-Ch		310		
Reverse Transfer Capacitance	C_{rss}	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$	N-Ch		65		pF
			P-Ch		75		
Total Gate Charge ²	Q_g	N-Channel $V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V,$ $I_D = 3A$	N-Ch		5		nC
			P-Ch		14		
Gate-Source Charge ²	Q_{gs}	P-Channel $V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = -10V,$ $I_D = -5A$	N-Ch		0.8		nC
			P-Ch		2.2		
Gate-Drain Charge ²	Q_{gd}		N-Ch		1.0		nC
			P-Ch		1.9		

Turn-On Delay Time ²	$t_{d(on)}$	N-Channel	N-Ch		7	11	nS
			P-Ch		6.7	13.4	
Rise Time ²	t_r	$V_{DD} = 10V$	N-Ch		12	18	
		$I_D \cong 1A, V_{GS} = 10V, R_{GEN} = 6\Omega$	P-Ch		9.7	19.4	
Turn-Off Delay Time ²	$t_{d(off)}$	P-Channel	N-Ch		12	18	
			P-Ch		19.8	35.6	
Fall Time ²	t_f	$V_{DD} = -10V$	N-Ch		7	11	
		$I_D \cong -1A, V_{GS} = -10V, R_{GEN} = 6\Omega$	P-Ch		12.3	22.2	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_c = 25 °C)

Continuous Current	I_S		N-Ch			1.2	A
			P-Ch			-1.3	
Pulsed Current ³	I_{SM}		N-Ch			2.6	
			P-Ch			-2.6	
Forward Voltage ¹	V_{SD}	$I_F = 1A, V_{GS} = 0V$	N-Ch			1	V
		$I_F = -1A, V_{GS} = 0V$	P-Ch			-1	

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

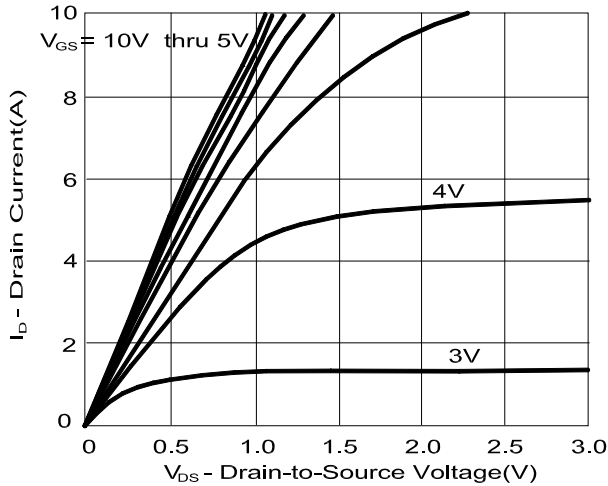
³Pulse width limited by maximum junction temperature.

REMARK: THE PRODUCT MARKED WITH “P4532VG”, DATE CODE or LOT #

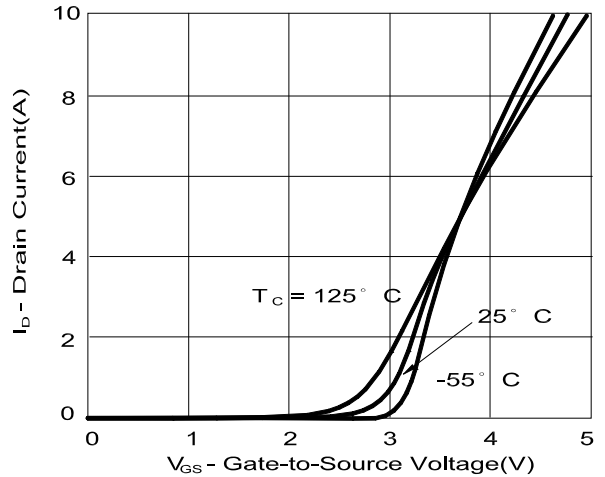
Orders for parts with Lead-Free plating can be placed using the PXXXXXG parts name.

N-CHANNEL

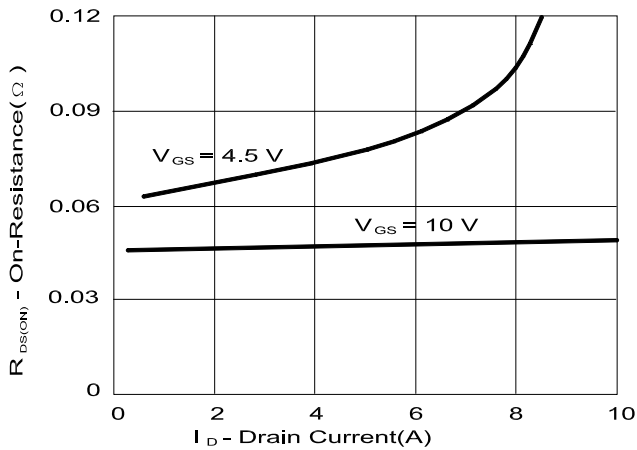
Output Characteristics



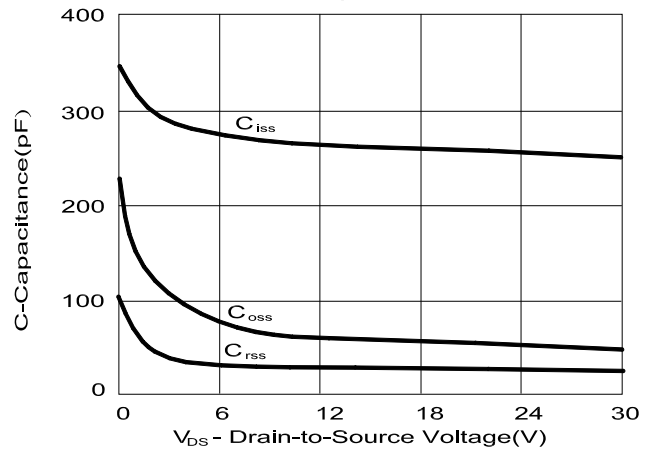
Transfer Characteristics



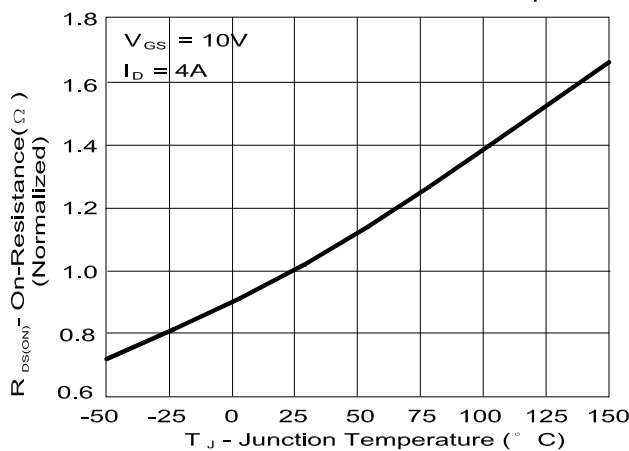
On-Resistance vs. Drain Current



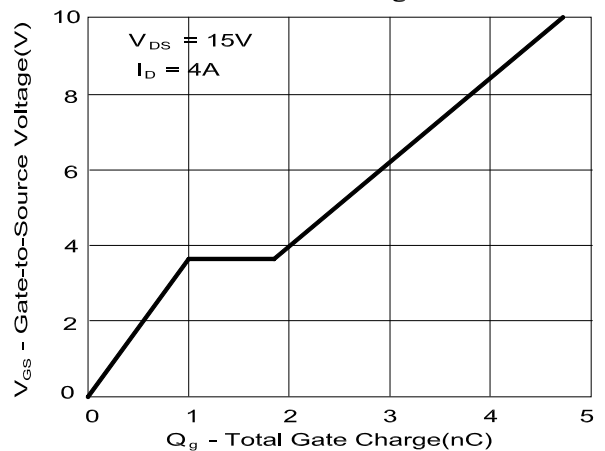
Capacitance

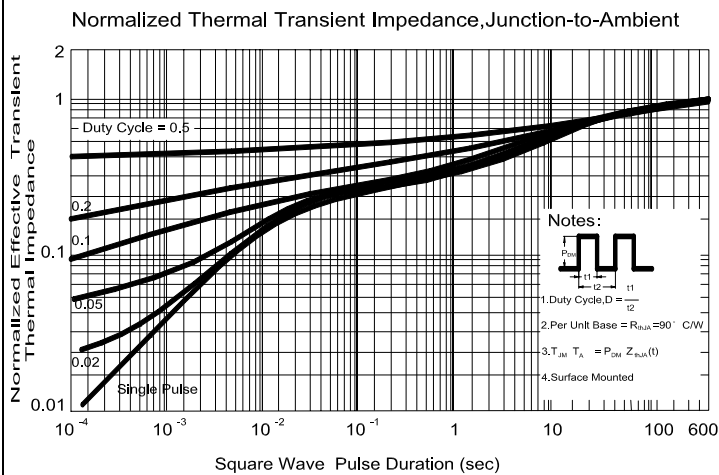
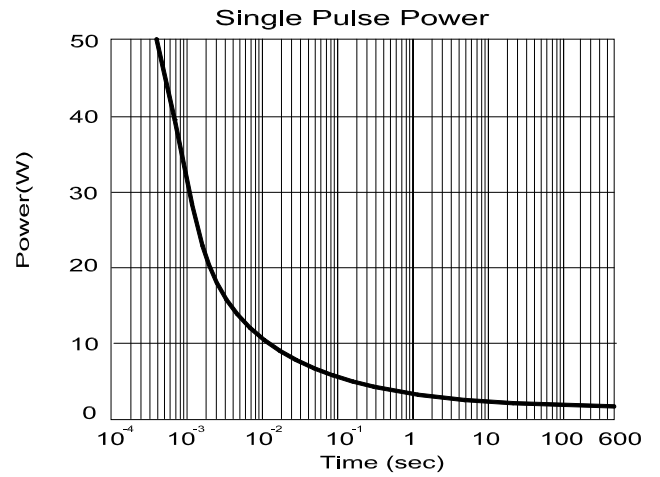
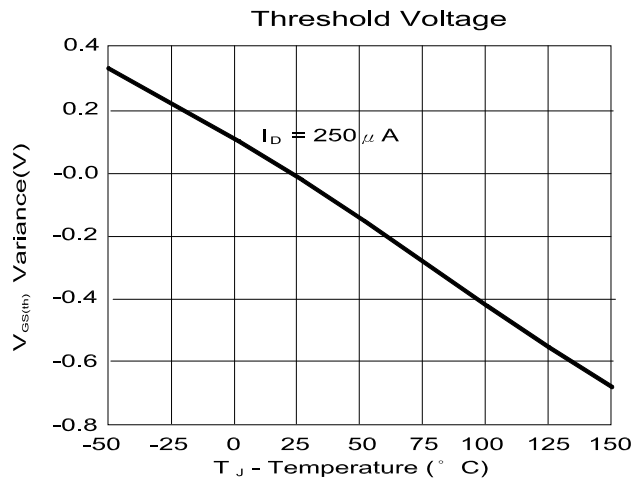
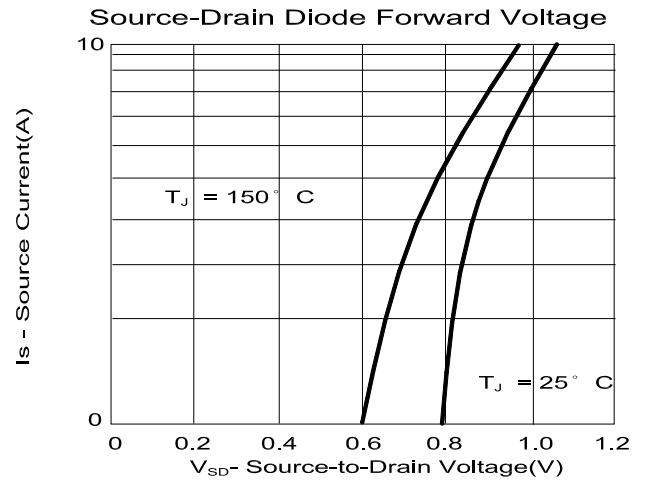
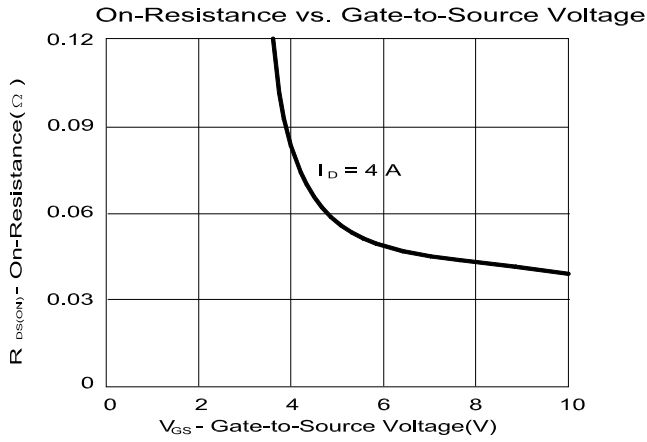


On-Resistance vs. Junction Temperature



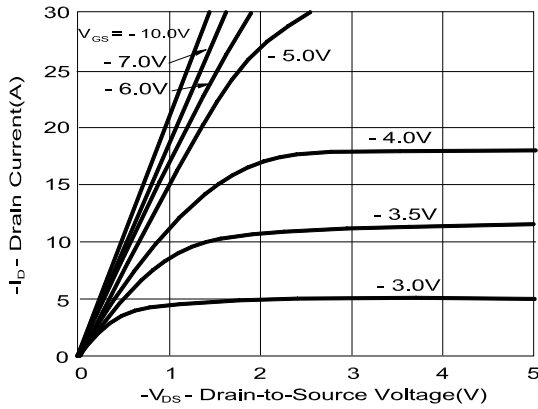
Gate Charge



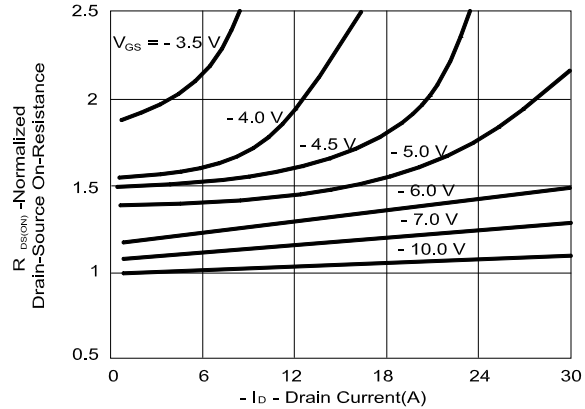


P-CHANNEL

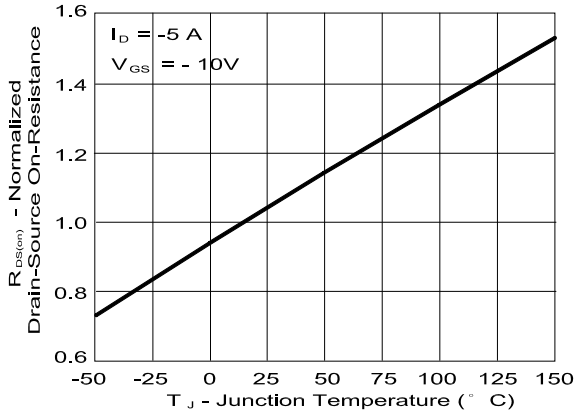
On-Region Characteristics



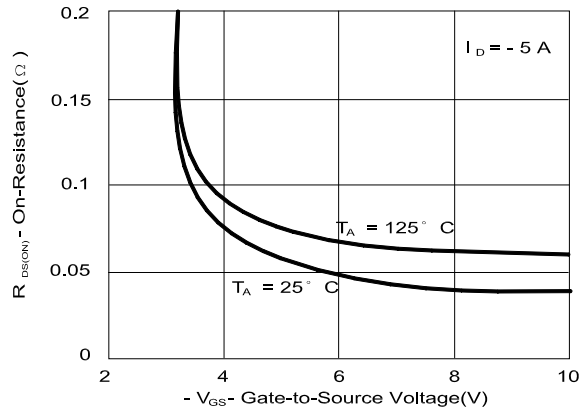
On-Resistance Variation with Drain Current and Gate Voltage



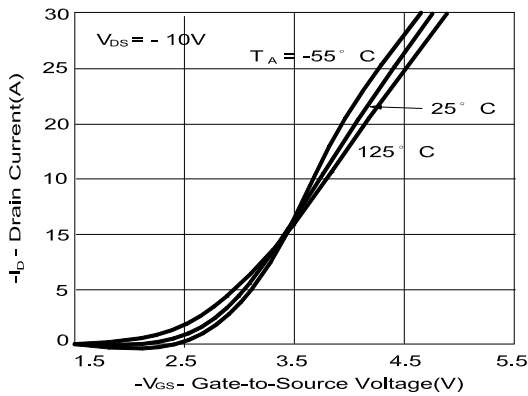
On-Resistance Variation with Temperature



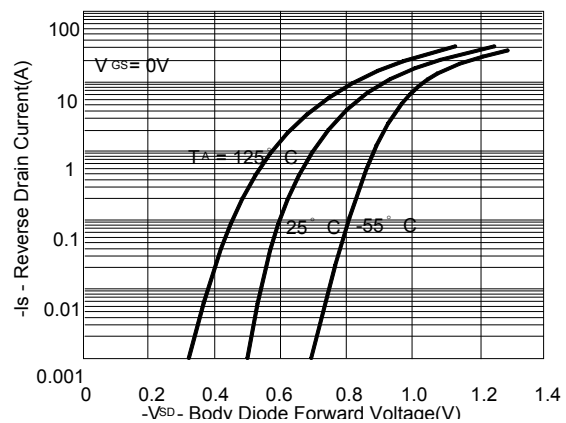
On-Resistance Variation with Gate-to-Source Voltage

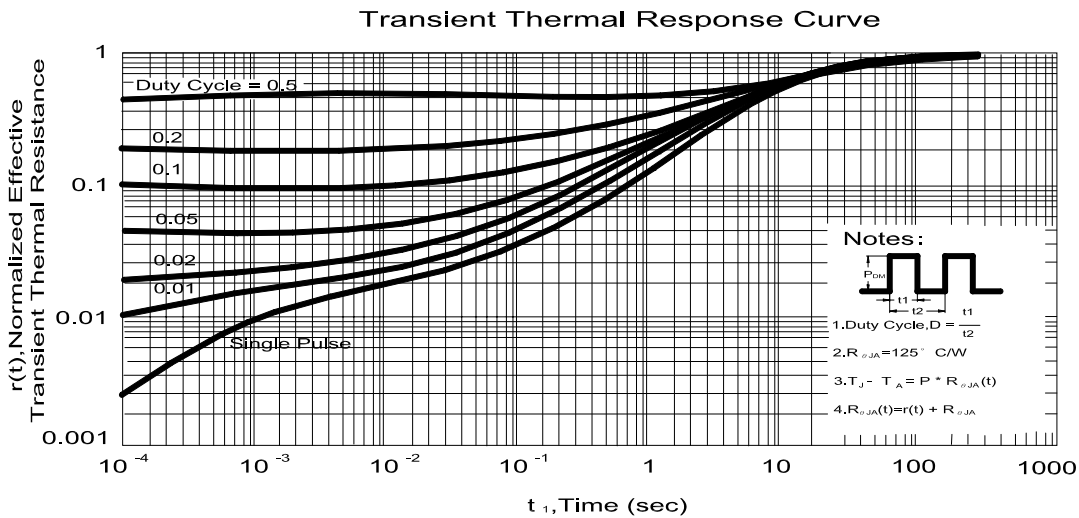
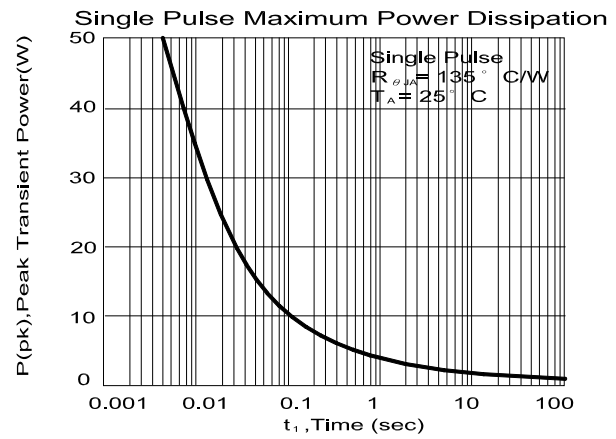
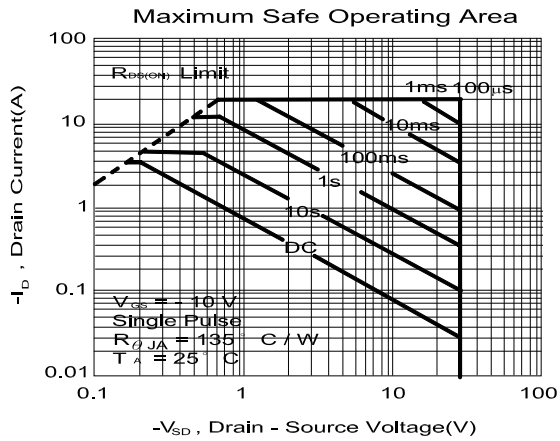
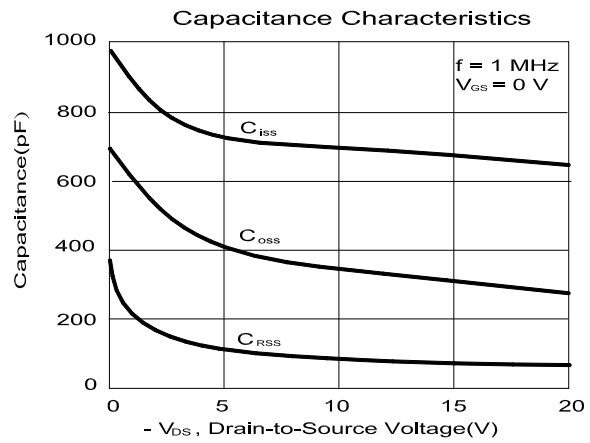
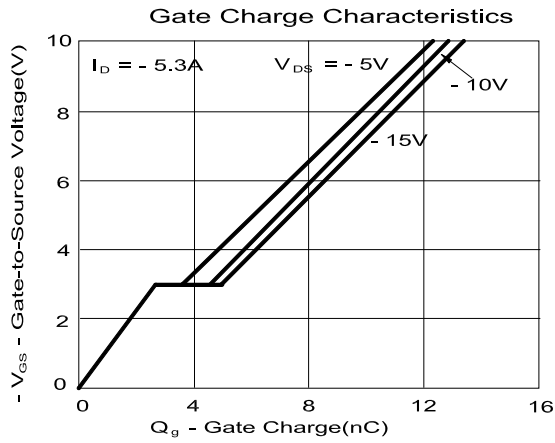


Transfer Characteristics



Body Diode Forward Voltage Variation with Source Current and Temperature





SOIC-8(D) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.5	0.715	0.83
B	3.8	3.9	4.0	I	0.18	0.254	0.25
C	5.8	6.0	6.2	J		0.22	
D	0.38	0.445	0.51	K	0°	4°	8°
E		1.27		L			
F	1.35	1.55	1.75	M			
G	0.1	0.175	0.25	N			

